

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

GS 162 D1

Application Number

Unassigned

Applicant(s)

Richard A. Blanchard

Filing Date

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Group Art Unit

2826

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TZ	1	5,744,719A	04-1998	Werner	73	514.32	
	2	5,895,951 A	04-1999	So et al.	257	330	
	3	6,184,555 B1	02-2001	Tihanyi et al.	257	342	
	4	5,216,275	6-1993	Chen	257	493	
	5	5,404,040	4-1995	Hshieh et al.	257	341	
	6	5,973,360	10-1999	Tihanyi	257	330	
	7	4,959,699	9-1990	Lidow et al.	357	23.7	
TZ	8	US-20020070418 A1	06-2002	Kinzer et al.	257	491	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
TZ	1	DE 198 00 647 C1	5/27/99	Germany	H01L29	78		✓
	2	DE 197 48 523 A1	5/12/99	Germany	H01L29	78		✓
	3	WO 99/23703	3/14/99	PCT	H01L29	06		✓
	4	EP 0 053 854 B1	5/2/86	EPO	H01L29	06	✓	
TZ	5	EP 0 973 203 A2	1/19/00	EPO	H01L29	06		✓

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

1	G. Deboy et al. "A New Generation of High Voltage MOSFETS Breaks The Limit Line of Silicon," Electron Devices Meeting, San Francisco, California, December 6-9 1998, Paper No. 26.2.1, pgs. 683-685, Sponsored by Electron Devices Society of IEEE.
2	T. Fujihira et al., "Simulated Superior Performances of Semiconductor Superjunction Devices," Proceedings of 1998 International Symposium on Power Semiconductor Devices & ICs, Kyoto, Japan, pp. 423-426.

EXAMINER

DATE CONSIDERED

12/08/04.

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

Jean-Marie Peter, "Power Semiconductors: New Devices Pursue Lower On-Resistance, Higher Voltage Operation," PCIM, January 1999, pp. 26-32.

"Power Semiconductors Proliferate: Expanding Product Lines and Advancing Process Technology Promise Higher Performance in Varied Applications," Electronic Products, July 1999, pp. 23-24.

L. Lorenz et al., "Improved MOSFET: An Important Milestone Toward A New Power MOSFET Generation," PCIM, September 1998, pp. 14-22.

X. Chen, "Optimum Design Parameters For Different Patterns of CB-Structure," Chinese Journal of Electronics, Vol. 9, No. 1, January 2000, pp. 6-11.

Jack Glenn et al., "A Novel Vertical Deep Trench RESURF DMOS (VTR-DMOS)," Proceedings of the 12th International Symposium on Power Semiconductor Devices & ICS, Toulouse, France, May 22-25, 2000, pp. 197-200.

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## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

	3	Chen, Xingbi, "Theory of a Novel Voltage Sustaining (CB) Layer For Power Devices," <i>Chinese Journal of Electronics</i> , Vol. 7, no. 3, July 1998, pp. 211-216.
	4	T. Fujihira, "Theory of Semiconductor Superjunction Devices," <i>Japanese Journal of Applied Physics</i> , Vol. 36 (1997), pp. 6254-6262.

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